


INFORMATION DISCLOSURE CITATION
(use several sheets if necessary)
ATTY DOCKET NO.
FIS920030245
SERIAL NO.
10/708,430
FILING DATE
3/3/04
GROUP
U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Al	6,228,694	5/8/01	Doyle et al.			
	6,406,973	6/18/02	Lee			
	6,281,532	8/28/01	Doyle et al.			
	5,683,934	11/4/97	Candelaria			
	6,368,931	4/9/02	Kuhn et al.			
	5,310,446	5/10/94	Konishi et al.			
	4,853,076	8/1/89	Tsaur et al.			
	2002/0090791	7/11/02	Doyle et al.			
	2002/0074598	6/20/02	Doyle et al.			
	6,509,618	1/21/03	Jan et al.			
Al	6,476,462	11/5/02	Shimizu et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER
DATE CONSIDERED
07/20/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

ATTY DOCKET NO.
PIS920030245

SERIAL NO.
10/708,430

FILING DATE
3/3/04

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Al	6,362,082	3/26/02	Doyle et al.			
	6,228,694	5/8/01	Doyle et al.			
	5,565,697	10/15/96	Asakawa et al.			
	2003/0040158	2/27/03	Saitoh			
	2002/0086472	7/4/02	Roberds et al.			
	6,521,964	2/18/03	Jan et al.			
	6,506,652	1/14/03	Jan et al.			
	5,081,513	1/14/92	Jackson et al.			
	3,602,841	8/31/71	McGroddy			
	6,531,740	3/11/03	Bosco et al.			
Al	6,531,369	3/11/03	Ozkan et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

Andy Kuey

DATE CONSIDERED

07/20/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

ATTY DOCKET NO.
FIS920030245

SERIAL NO.
10/708,430

FILING DATE
3/3/04

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>Alb</i>	5,940,736	8/17/99	Brady et al.			
	5,880,040	3/9/99	Sun et al.			
	5,861,651	1/19/99	Brasen et al.			
	5,679,965	10/21/97	Schetzina			
	5,670,798	9/23/97	Schetzina			
	5,561,302	10/1/96	Candelaria			
	5,471,948	12/5/95	Burroughes et al.			
	5,459,346	10/17/95	Asakawa et al.			
	5,391,510	2/21/95	Hsu et al.			
	5,371,399	12/6/94	Burroughes et al.			
<i>Alb</i>	5,108,843	4/28/92	Ohtaka et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

Andy Newell

DATE CONSIDERED

07/20/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

ATTY DOCKET NO.
FIS920030245

SERIAL NO.
10/708,430

FILING DATE
3/3/04

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Alh	5,060,030	10/22/91	Hoke			
	4,958,213	9/18/90	Eklund et al.			
	4,665,415	5/12/87	Esaki et al.			
	5,989,978	11/23/99	Peidous			
	6,284,626	9/4/01	Kim			
	6,274,444	8/14/01	Wang			
	6,261,964	7/17/01	Wu et al.			
	6,221,735	4/24/01	Manley et al.			
	6,117,722	9/12/00	Wuu et al.			
	6,107,143	8/22/00	Park et al.			
Alh	6,090,684	7/18/00	Ishitsuka et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

Andy Murray

DATE CONSIDERED

07/20/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)			ATTY DOCKET NO. FIS920030245		SERIAL NO. 10/708,403	
			FILING DATE 3/3/04	GROUP		
U.S. PATENT DOCUMENTS						
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>Al</i>	6,066,545	5/23/00	Doshi et al.			
	6,008,126	12/28/99	Leedy			
	5,946,559	8/31/99	Leedy			
	5,840,593	11/24/98	Leedy			
	5,592,018	1/7/97	Leedy			
	5,592,007	1/7/97	Leedy			
	5,571,741	11/5/96	Leedy			
	5,557,122	9/17/96	Shrivastava et al.			
	5,354,695	10/11/94	Leedy			
	5,134,085	7/28/92	Gilgen et al.			
<i>Al</i>	5,006,913	4/9/91	Sugahara et al.			
FOREIGN PATENT DOCUMENTS						
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
EXAMINER <i>Andy Neary</i>			DATE CONSIDERED <i>07/26/05</i>			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

ATTY DOCKET NO.
FIS920030245

SERIAL NO.
10/708,403

FILING DATE
3/3/04

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Alh	4,952,524	8/28/90	Lee et al.			
	4,855,245	8/8/89	Neppl et al.			
	2002/0086497	7/4/02	Kwok			
	5,960,297	9/28/99	Saki			
	6,403,486	6/11/02	Lou			
	6,284,623	9/4/01	Zhang et al.			
	2003/0032261	2/13/03	Yeh et al.			
	2003/0057184	3/27/03	Yu et al.			
	6,265,317	7/24/01	Chiu et al.			
	2003/0067035	4/10/03	Tews et al.			
Alh	6,461,936	10/8/02	von Ehrenwall			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

Andy Nguyen

DATE CONSIDERED

07/20/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Supplemental Form PTO-1449 (Modified)		Attorney Docket No.:	Serial No.:
		FIS920030245US1	1,0708,430
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		Applicant:	SC89 43031 P.E.
(Use several sheets if necessary)		Michael P. Belyansky, et al.	JUN 28 2004
Page 1 of 1.		Filing Date:	Group:
		3/3/04	

REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS					
EXAMINERS INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)	

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

<i>Ah</i>		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si <i>n</i> -MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99.
		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
		F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Devices Meeting, 23.5.1, IEEE, April 2000.
		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
		A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001.
<i>Ah</i>		K. Ota, et al., "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002.

EXAMINER	DATE CONSIDERED
	57 to 05

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.